



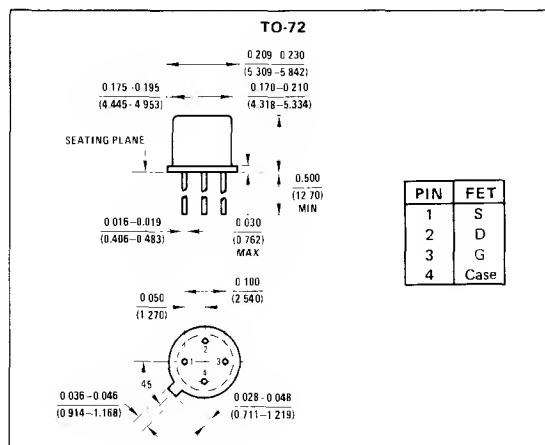
2N5358-60 N-Channel JFETs

General Description

The 2N5358 thru 2N5360 series of N-channel JFETs is characterized for general purpose audio and RF amplifiers requiring tightly specified IDSS ranges.

Absolute Maximum Ratings (25°C)

Gate-Drain or Gate-Source Voltage	-40V
Gate Current	10 mA
Total Device Dissipation (25°C Free-Air Temperature)	300 mW
Power Derating (to +175°C)	2 mW/°C
Storage Temperature Range	-65°C to +200°C
Operating Temperature Range	-65°C to +175°C
Lead Temperature (1/16" from case for 10 seconds)	300°C



Electrical Characteristics (25°C unless otherwise noted)

PARAMETER	CONDITIONS	2N5358		2N5359		2N5360		UNITS
		MIN	MAX	MIN	MAX	MIN	MAX	
IGSS	Gate Reverse Current VDS = 0, VGS = -20V T = 150°C	-100		-100		-100		pA
VGS(off)	Gate-Source Cutoff Voltage VDS = 15V, ID = 100 nA	-0.5	-3.0	0.8	-4.0	-0.8	-4.0	nA
BVGSS	Gate-Source Breakdown Voltage VDS = 0, IG = -10 μA	-40		-40		-40		V
IDSS	Saturation Drain Current VDS = 15V, VGS = 0, (Note 1)	0.5	1.0	0.8	1.6	1.5	3.0	mA
VGS	Gate-Source Voltage VDS = 15V, ID = (Note 2)	0.3	-1.5	-0.4	-2.0	-0.5	-2.5	V
gfs	Common-Source Forward Transconductance VDS = 15V, VGS = 0	f = 1 kHz	1000	3000	1200	3600	1400	4200
Vfs	Common-Source Forward Transadmittance	f = 100 MHz	800		900		1400	
goss	Common-Source Output Conductance	f = 1 kHz		10		10		20
Crss	Common-Source Reverse Transfer Capacitance	f = 1 MHz		2		2		pF
Ciss	Common-Source Input Capacitance	f = 100 Hz, RG = 1 MΩ		6		6		
NF	Noise Figure	f = 100 Hz, RG = 1 MΩ		2.5		2.5		dB

Note 1: Pulse test duration = 300 μs. Duty cycle ≤ 3%.

Note 2: ID test conditions for Test 5: 2N5358 = 50 μA; 2N5359 = 80 μA; 2N5360 = 150 μA